Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1240 mW

3. Applications

- Relay driver
- · High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-3.9	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -3.1 A; T_j = 25 °C		-	72	88	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate	□	G T
4	S	source		\$ 017aaa257
5	D	drain		
6	D	drain		

6. Ordering information

Table 3. Ordering information

	Type number	Package					
		Name	Description	Version			
	PMN70XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN70XP	H5

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j = 25 °C		-	-20	V
gate-source voltage			-12	12	V
drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-3.9	Α
	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.1	Α
	V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2	Α
peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-13	Α
total power dissipation	T _{amb} = 25 °C	[2]	-	530	mW
		[1]	-	1.24	W
	T _{sp} = 25 °C		-	4.46	W
junction temperature			-55	150	°C
ambient temperature			-55	150	°C
storage temperature			-65	150	°C
diode					1
source current	T _{amb} = 25 °C	[1]	-	-1.2	Α
	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature	$ \begin{array}{lll} & & & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & & \\ & $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{drain-source voltage} \\ \text{gate-source voltage} \\ \end{array} \begin{array}{c} T_{j} = 25 ^{\circ}\text{C} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = -4.5 \text{V}; T_{amb} = 25 ^{\circ}\text{C}; t \leq 5 \text{s} \\ \end{array} \begin{array}{c} \text{[1]} \\ -12 \\ \end{array} \\ V_{GS} = -4.5 \text{V}; T_{amb} = 25 ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[1]} \\ -12 \\ \end{array} \\ V_{GS} = -4.5 \text{V}; T_{amb} = 25 ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[1]} \\ -12 \\ \end{array} \\ \text{peak drain current} \\ \end{array} \begin{array}{c} T_{amb} = 25 ^{\circ}\text{C}; \text{single pulse}; t_{p} \leq 10 \mu\text{s} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \text{total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} = 25 ^{\circ}\text{C}; \text{single pulse}; t_{p} \leq 10 \mu\text{s} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \text{In total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} = 25 ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[2]} \\ -13 \\ \end{array} \\ \end{array} \begin{array}{c} -12 \\ \end{array} \\ \end{array} \\ \text{In total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} = 25 ^{\circ}\text{C} \\ \end{array} \begin{array}{c} \text{[1]} \\ -13 \\ \end{array} \\ \end{array} \begin{array}{c} -13 \\ \end{array} \\ \end{array} \\ \text{Junction temperature} \\ \end{array} \begin{array}{c} -55 \\ \end{array} \\ \text{ambient temperature} \\ \end{array} \begin{array}{c} -55 \\ -55 \\ \end{array} \\ \text{storage temperature} \\ \end{array} \begin{array}{c} -65 \\ \end{array} \\ \end{array} $	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

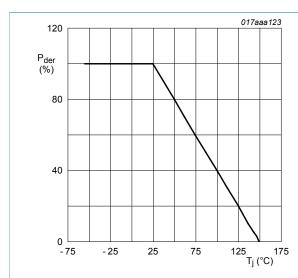


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

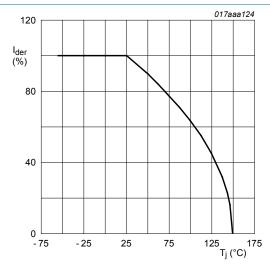


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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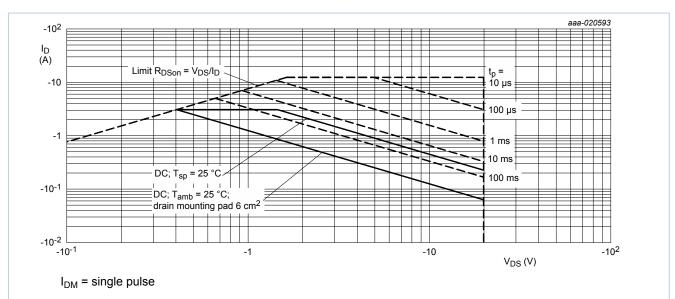


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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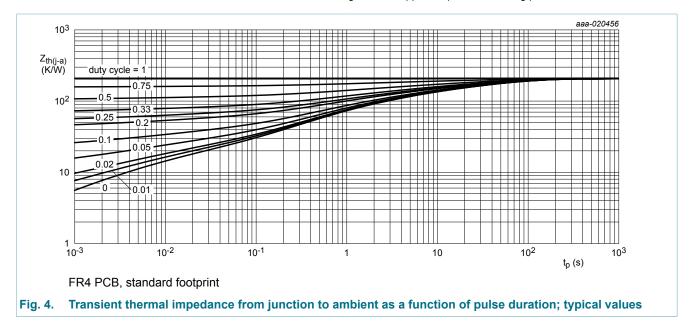
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9. Thermal characteristics

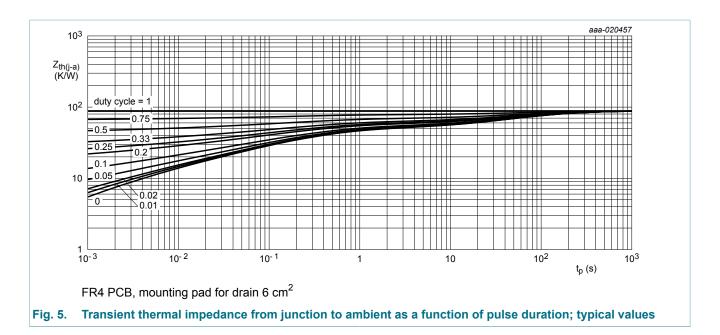
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uity a)	thermal resistance	in free air	[1]	-	205	235	K/W
	from junction to ambient		[2]	-	88	101	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	55	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	24	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.47	-0.65	-0.9	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -3.1 A; T_j = 25 °C	-	72	88	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -3.1 A; T _j = 150 °C	-	107	130	mΩ
		V_{GS} = -2.5 V; I_D = -2.6 A; T_j = 25 °C	-	88	116	mΩ
		V _{GS} = -1.8 V; I _D = -0.7 A; T _j = 25 °C	-	110	170	mΩ
		V_{GS} = -1.5 V; I_D = -0.1 A; T_j = 25 °C	-	150	360	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C	-	15	-	S
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2.5 A; V_{GS} = -4.5 V;	-	5	7.5	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	550	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	63	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2.5 A; V_{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	120	-	ns
t _f	fall time		-	50	-	ns
Source-dra	in diode		l I	1	1	
V_{SD}	source-drain voltage	I _S = -1.2 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.9	-1.2	V

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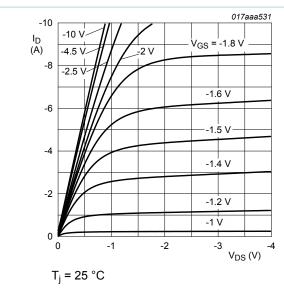


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

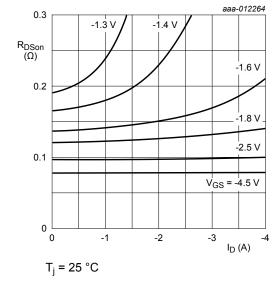


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

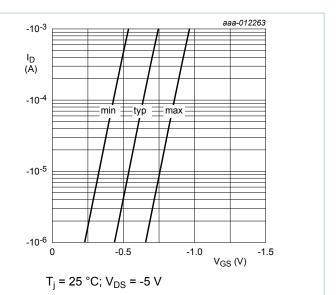


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

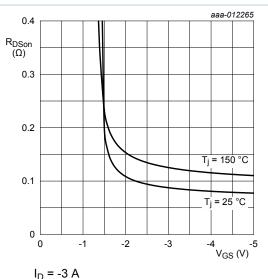


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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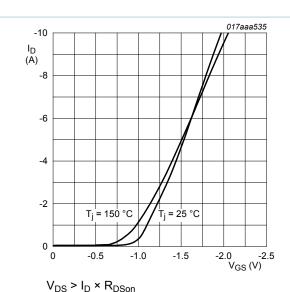


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

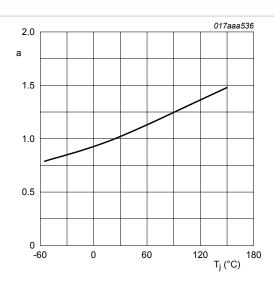


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

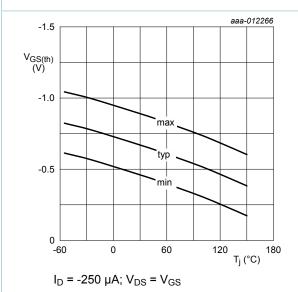


Fig. 12. Gate-source threshold voltage as a function of junction temperature

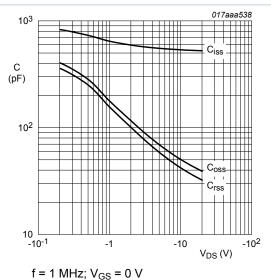


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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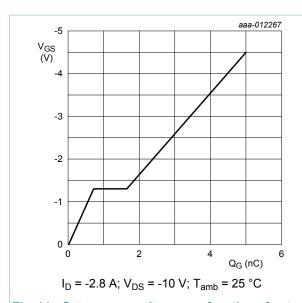


Fig. 14. Gate-source voltage as a function of gate charge; typical values

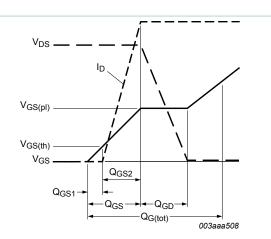


Fig. 15. MOSFET transistor: Gate charge waveform definitions

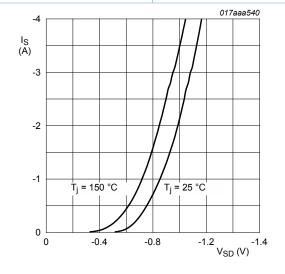
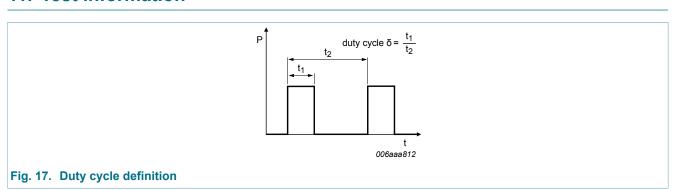


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



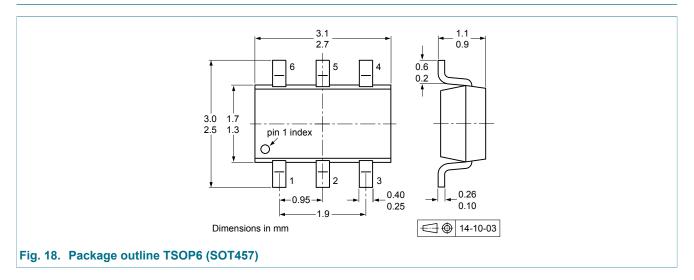
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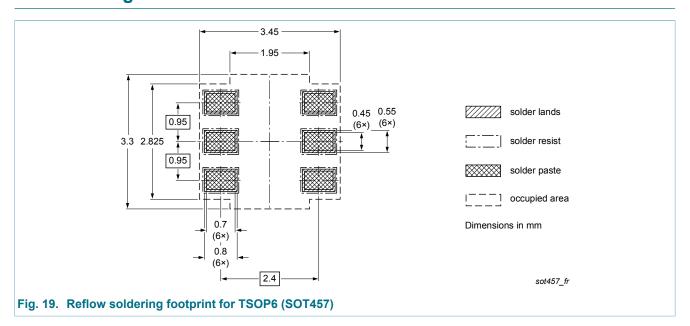
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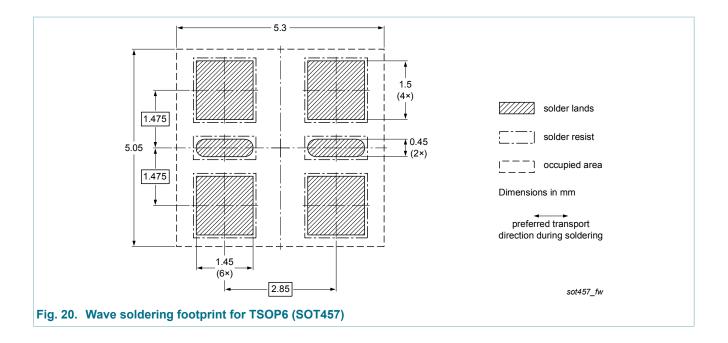
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN70XP v.1	20160129	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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